

SEMITOP® 3

3-phase bridge rectifier+ series thyristor

SK 30 DTA

Target Data

Features

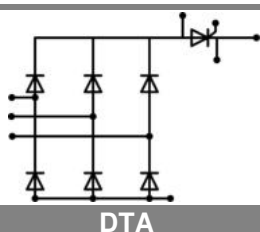
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passivated thyristor chips
- Reverse voltage up to 1600 V
- High surge currents

Typical Applications*

- Soft starters
- Light control
- Temperature control

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 25$ A ($T_s = 80$ °C)
900	800	SK 30 DTA 08
1300	1200	SK 30 DTA 12
1700	1600	SK 30 DTA 16

Characteristics $T_s = 25$ °C unless otherwise specified			
Symbol	Conditions	Values	Units
I_D	$T_s = 80$ °C; Ind. load	25	A
I_{TAV}	sin. 180°; $T_s = 25$ (80) °C per thyristor	31 (19)	A
I_{FAV}	sin. 180°; $T_s = 25$ (80) °C per diode	37 (25)	A
I_{TSM}/I_{FSM}	$T_{vj} = 25$ (125) °C; 10 ms	1000 (900)	A
I^2t	$T_{vj} = 25$ (125) °C; 8,3 ... 10 ms	5000 (4000)	A²s
T_{stg}		-40,...+125	°C
T_{solder}	terminals, 10 s	260	°C
Thyristor			
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	1000	V/μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C; $f = 50 \dots 60$ Hz	50	A/μs
t_q	$T_{vj} = 125$ °C; typ.	80	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	100 / 200	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33 \Omega$; typ. / max.	200 / 400	mA
V_T	$T_{vj} = 25$ °C; ($I_T = 120$ A); max.	1,8	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 1	V
r_T	$T_{vj} = 125$ °C	max. 6	mΩ
I_{DD}, I_{RD}	$T_{vj} = 125$ °C; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$	max. 8	mA
$R_{th(j-s)}$	Cont. per thyristor	0,8	K/W
T_{vj}		- 40 ... + 125	°C
V_{GT}	$T_{vj} = 25$ °C; d.c.	2	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	100	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	5	mA
Diode			
V_F	$T_{vj} = 25$ °C; ($I_F = 25$ A); max.	1,25	V
$V_{(TO)}$	$T_{vj} = 150$ °C	0,8	V
r_T	$T_{vj} = 150$ °C	4	mΩ
I_{RD}	$T_{vj} = 150$ °C; $V_{RD} = V_{RRM}$	4	mA
$R_{th(j-s)}$	per diode	1,7	K/W
T_{vj}		-40...+150	°C
Mechanical data			
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min	3000 (2500)	V
M_1	mounting torque	2,5	Nm
w		30	g
Case	SEMITOP® 3	T 45	



DTA

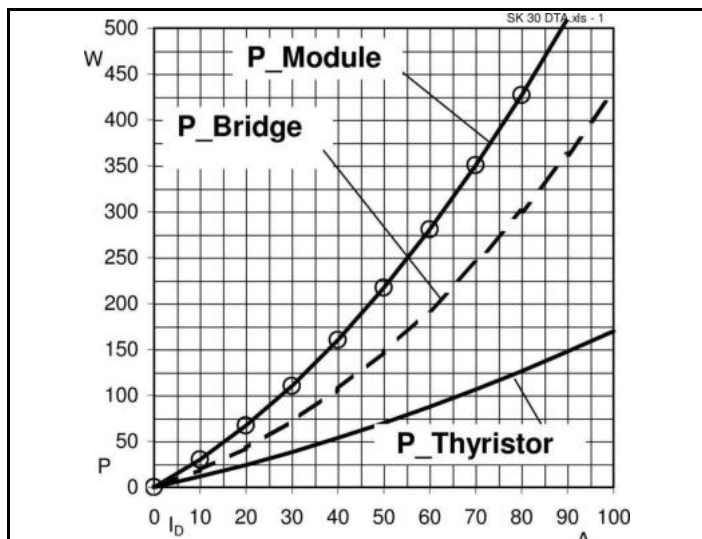


Fig. 1 Power dissipation per module vs. output bridge current

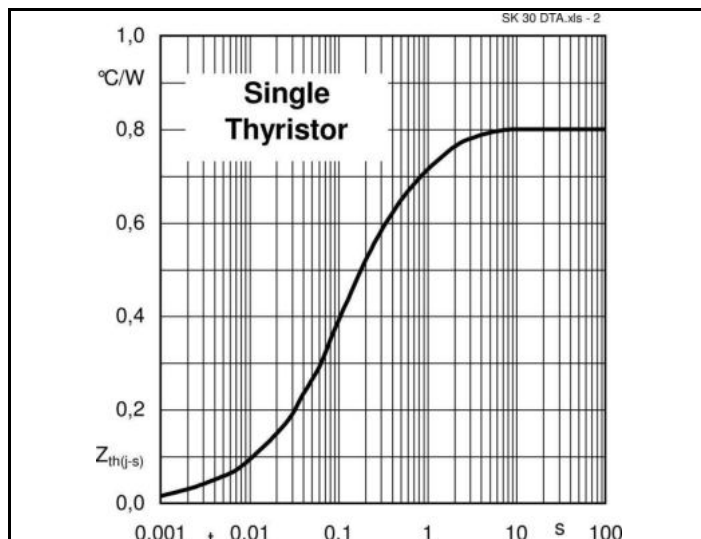


Fig. 2 Transient thermal impedance vs time

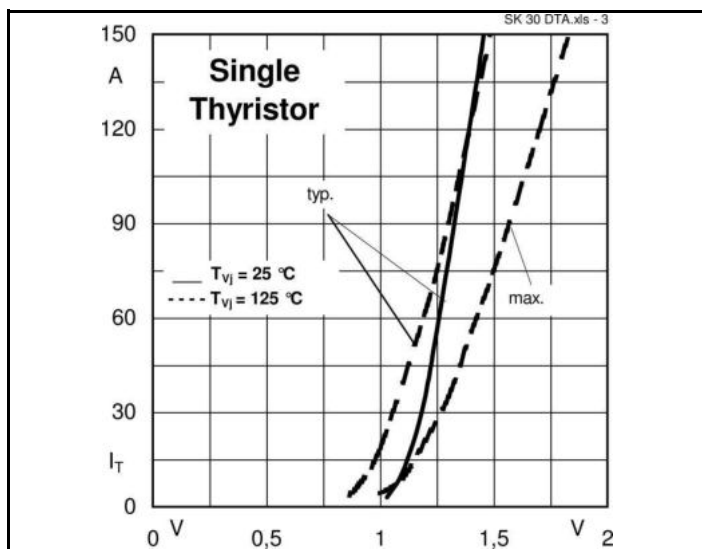


Fig. 3a Thyristor On-state characteristics

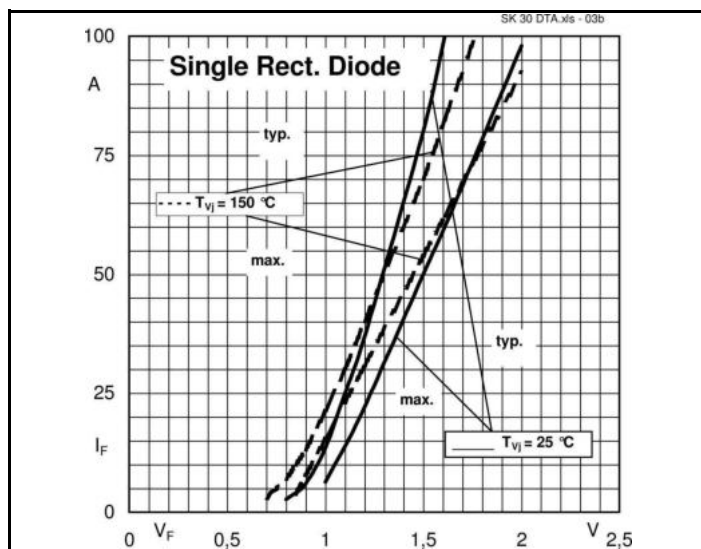


Fig. 3b Rect. Diode On-state characteristics

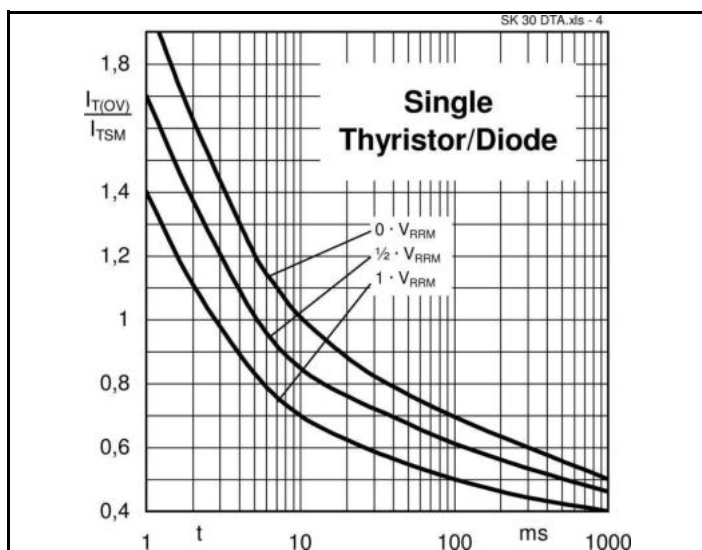


Fig. 4 Surge overload current vs. time

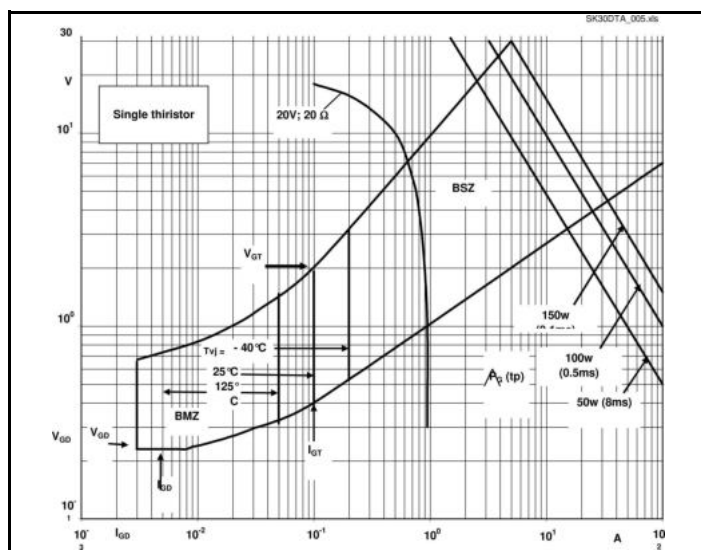
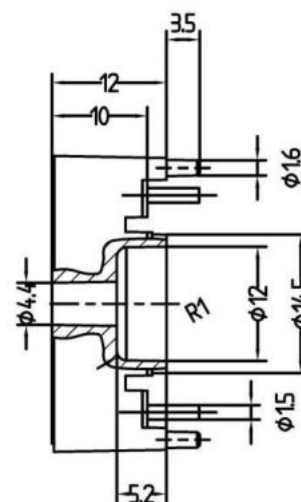
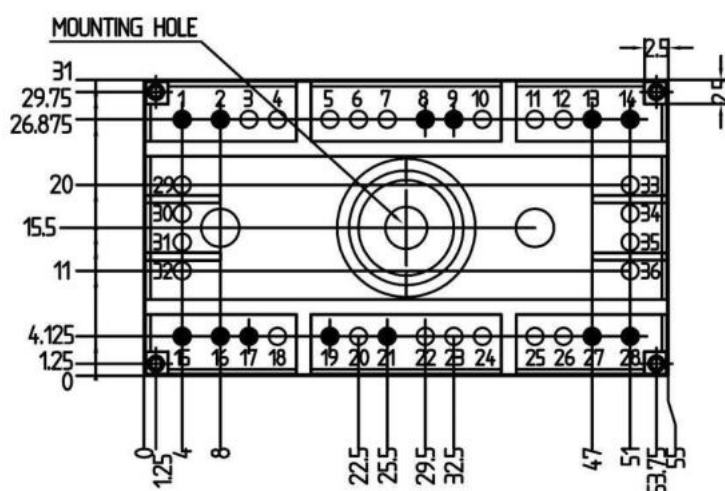
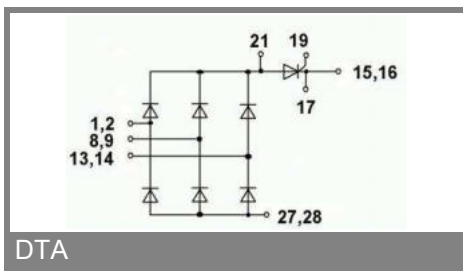


Fig. 5 Gate trigger characteristics

Technical drawing of the bottom view of a printed circuit board (Lato stampigliatura). The drawing shows the layout of components and dimensions. Dimensions include 34.3, 10.5, and 67.5. Component locations are marked with circled numbers 1 through 28.



Case T45 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.